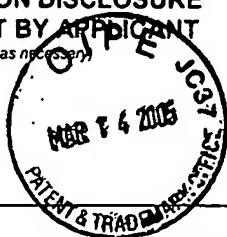


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Filing Date	June 24, 2003
First Named Inventor	Ahn, Kie
Group Art Unit	2829
Examiner Name	Sarkar, Asok

Sheet 1 of 1

Attorney Docket No: 1303.107US1

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date If Appropriate
AKS	US-2004/0144980-A1	07/29/2004	Ahn, Kie Y., et al.	01/29/2003
	US-2005/0020017-A1	01/27/2005	Ahn, K. Y., et al.	06/24/2003
	US-3,357,961	12/12/1967	Makowski, H. S., et al.	05/24/1965
	US-5,572,052	11/05/1996	Kashihara, K., et al.	01/19/1995
	US-6,632,279	10/14/2003	Ritala, M., et al.	10/13/2000
	US-6,674,138	01/06/2004	Halliyal, A., et al.	12/31/2001
	US-6,699,747	03/02/2004	Ruff, Alexander, et al.	11/18/2002
AKS	US-6,831,315	12/14/2004	Raaijmakers, Ivo, et al.	02/22/2001

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	T ²
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
AKS		CHIN, A., et al., "High Quality La ₂ O ₃ and Al ₂ O ₃ Gate Dielectrics with Equivalent Oxide Thickness 5-10A", <u>Digest of Technical Papers. 2000 Symposium on VLSI Technology, 2000, Honolulu, (June 13-15, 2000), 16-17</u>	
		COPEL, M., et al., "Formation of a stratified lanthanum silicate dielectric by reaction with Si(001)", <u>Applied Physics Letters, 78(11), (March 12, 2001), 1607-1609</u>	
		DIMOULAS, A., et al., "Structural and electrical quality of the high-k dielectric Y ₂ O ₃ on Si (001): Dependence on growth parameters", <u>Journal of Applied Physics, 92(1), (July 1, 2002), 426-431</u>	
		GUHA, S., et al., "Atomic beam deposition of lanthanum-and yttrium-based oxide thin films for gate dielectrics", <u>Applied Physics Letters, 77, (2000), 2710-2712</u>	
		HUANG, C. H., et al., "La/sub 2/O/sub 3/Si/sub 0.3/Ge/sub 0.7/ p-MOSFETs with high hole mobility and good device characteristics", <u>IEEE Electron Device Letters, 23(12), (December 2002), 710-712</u>	
		IWAI, H., et al., "Advanced gate dielectric materials for sub-100 nm CMOS", <u>International Electron Devices Meeting, 2002. IEDM '02. Digest., (December 8-11, 2002), 625-628</u>	
		MARIA, J. P., et al., "High temperature stability in lanthanum and zirconia-based gate dielectrics", <u>Journal of Applied Physics, 90(7), (Oct. 1, 2001), 3476-3482</u>	
		MICHAELSON, HERBERT B., "The work function of the elements and its periodicity", <u>Journal of Applied Physics, 48(11), (November 1977), 4729-4733</u>	
AKS		YAMADA, HIROTOSHI, et al., "MOCVD of High-Dielectric-Constant Lanthanum Oxide Thin Films", <u>Journal of The Electrochemical Society, 150(8), (August 2003), G429-G435</u>	

EXAMINER

Asok Kumar Sarkar

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